NOVEL MATERIALS AND INNOVATIVE SEMICONDUCTORS

NH3T010MP120F2

1200 V 10 mΩ Silicon **Carbide Half-Bridge Power Module**

V_{DS}	l _D	R _{DS(on)}	Configuration
1200 V	200 A	10 mΩ	Half-Bridge

Features

- State-of-the-art SiC MOSFET technology
- Reliable gate oxide process
- 100% avalanche tested
- Press-fit package for design flexibility
- Baseplate-less for low thermal resistance

Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency
- Enhanced system reliability
- Reduced total harmonic distortion



Applications

- Motor drives
- Solar PV inverters
- EV onboard chargers
- Server power supplies
- Energy storage systems
- EV fast charging stations
- Solid-state power controllers
- Uninterruptible power supplies

Maximum Ratings

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	Note
Drain-Source Voltage	V _{(BR)DSS}	T _C = 25 ° C	1200	-	-	٧	
Gate-Source Voltage	V _{GS(max)}		-10	-	25		
	$V_{GS,op}$	Recommended Operation	-	-5/+20	-	\ \	
Continuous Drain Current	I _D	V _{GS} = 20 V, T _C = 25 °C	-	-	200	- А	
		V _{GS} = 20 V, T _C = 100 °C	-	-	200		
Pulsed Drain Current	I _{D(pulse)}	$T_C = 25$ °C t_P limited by $T_{j(max)}$	-	-	400	Α	
Operating and Storage Temperature	T_J , T_stg		-55	-	175	°C	

NTC Thermistor Characterization

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	Note
Rated Resistance	R _{NTC}	25±0.05 ° c	4.75	5.0	5.25	kΩ	Fig. 1
Beta Value	β _{25/50}	25±0.05 ° c ,50±0.05 ° c	3312	3380	3448	K	
Time Constant	τ	In still air	1	≤10	1	S	
Dissipation Factor	δ	In still air	ı	≥2.4	ı	mW/°C	
Power Dissipation	P _{Max}	Ambient temperature+25°C	-	80	-	mW	

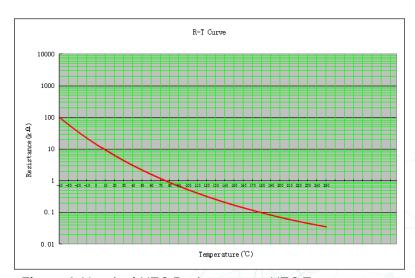
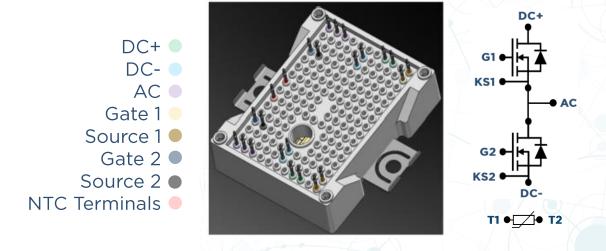


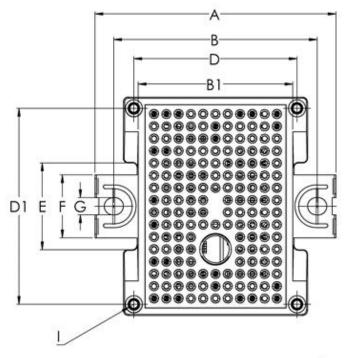
Figure 1: Nominal NTC Resistance vs. NTC Temperature

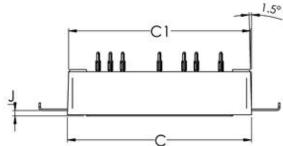
Pinout



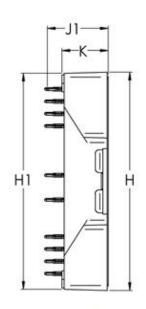
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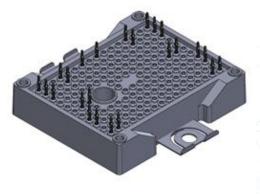
Package Dimensions











Note:

- Signal Pin hole grid 3.2mm
- Tolerance of hole pattern 🕁 0.1



- Signal Pin drill diameter 1.30mm
- Rib matrix thickness 0.9 ±0.2mm
- Brace thickness 0.4mm

Material:

- 1. Plastic Case PBT+30%GF (D202G30 White)
- Cosmetic Treatment Polish (#1000 #2000)

12.05

12.40

11.70

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